

RAJ2800024H11HPF

R07DS1394EJ0101 Rev. 1.01 Feb. 14. 2022

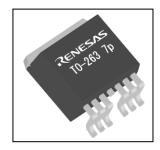
Intelligent Power Device for automotive application

1. Overview

1.1 Description

Family:

RAJ280002 is 1.6mohm single channel Intelligent Power Devices (IPD) embedded in TO263-7 package. It is N-channel high-side switches with charge pump, diagnostic feedback with proportional load current sense and embedded protection function. Family includes up to 4 devices depending on on-state resistance, input interface combination between current driven and voltage driven.



Scalability:

Variety of on-state resistance combined with standardized package on pin-out give user high flexibility for unit design depending on target load.

Robustness:

Because of advanced protection method, RAJ280002 achieves high robustness against long term and repetitive short circuit condition.

1.2 Features

- Built-in charge pump
- Low standby current
- Short circuit protection
- Shutdown by over current detection
- Power limitation protection by over load detection (Power limitation: current limitation with delta Tch control)
- Shutdown by absolute channel over temperature detection
- Built-in diagnostic function
 - Proportional load current sensing
 - Defined fault signal in case of abnormal load condition
- Reverse battery protection by self-turn ON
- Under voltage lock out
- Active clamp operation at inductive load switch off
- AEC Qualified
- RoHS compliant

1.3 Product summary

Parameter	Symbol	Values
Operating Voltage	VCC	4.5V to 28V
Under voltage shutdown	VCC(Uv)	Max. 4.5V
On-state resistance at 25 degreeC	Ron	Max. 2.0mohm, Typ. 1.6mohm
Inductive load switch-off energy dissipation single pulse	EAS	1700mJ
Inductive load switch-off energy dissipation repetitive pulse	EAR	840mJ
Minimum Over current detection current	IL(SC)	150A

1.4 Application

- All types of resistive, inductive and capacitive loads, especially for high current loads.
- Power management application such as Power distribution switches, Heaters, glow plugs, etc

NOTE: The information contained in this document is the one that was obtained when the document was issued, and may be subject to change.

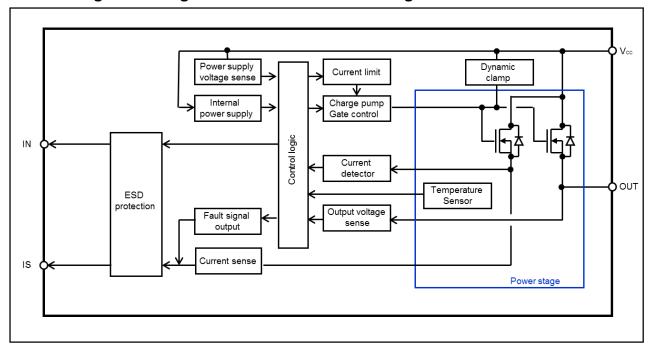
2. Ordering Information

Part No.	Lead plating	Packing	Package
RAJ2800024H11HPF	Pure Matte Sn	Tape 800pcs/reel	TO263-7

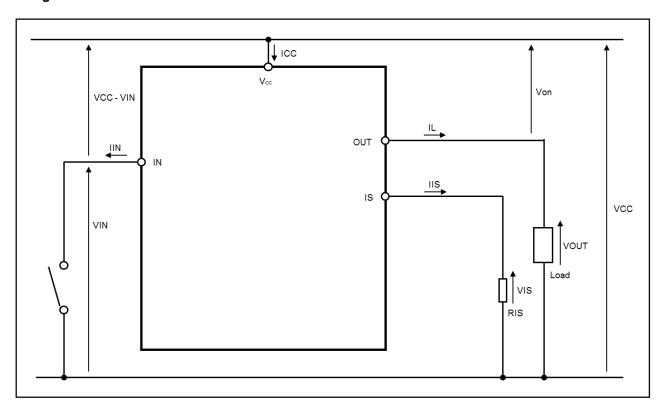
3. Specification

3.1 Block Diagram

3.1.1 Nch High-side Single Channel Device Block Diagram



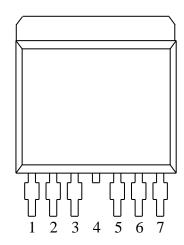
Voltage and Current Definition



3.2 Pin Configuration

3.2.1 TO263-7 Pin Configuration

Pin No.	Terminal Name
1	IN
2	N.C.
3	IS
4, Tab	VCC
5	OUT
6	OUT
7	OUT



Pin function

Terminal Name	Pin function	Recommended connection			
IN	Activates the output, if it shorted to ground	Connected to GND through a 100 ohm resistor and switch			
IS	Current sense and Diagnosis output signal	Connected to GND through a 1k-6k ohm resistor			
OUT	Protected high-side power output	Connected to load with 50-100nF capacitor in parallel			
VCC	Positive power supply for output power supply	Connected to battery voltage with 100nF capacitor in parallel			

¹⁾ A resistor is necessary to satisfy Von, clamp characteristics

3.3 Absolute Maximum Ratings

Stress values that exceed those listed here may cause permanent damage to the device. Exposure to absolute maximum rating condition for extended periods may affect device reliability.

Integrated protection functions are designed to prevent IC destruction under fault condition described in the data sheet. Fault conditions are considered as out of normal operation. Protection function shall not be intended to be used for continuous repetitive operation.

Ta=25degreeC, unless other specified

Symbol	Rating	Unit	Test Condition		
V_{CC}	28	V			
-V _{CC}	-16	V	At nominal load current, t<2min,		
			RIN=10	00ohm, RIS=1kohm	
V _{load dump}	42	V			1kohm,
,			RIN=10	00ohm, td=400ms,	
IL	Self limited	Α			
P_{D}	3.10	W			
					poxy PCB FR4
				cm2 of 70 um copper area	
V_{IN}		V			
	Vcc+16			-	n,
				00ohm	
VIS	-2 to VCC	V	_		
-					
	-16	V	•		n,
			,		
IIS(Rev)	-30	mA			n,
			RL= Nominal load		
Tch	-40 to +150	degreeC			
-		V	HBM	AFC-Q100-002 std.	All pin
LOD	2000	•	1.5		, p
_					
	4000				
					VCC, OUT
=		.,			
	200	V	MM		
5.0	4700		1/00 /		
EAS	1700	mJ			eC,
			RL=NO	minai load, Refer to 3.6.6	
FΔR	840	m I	VCC-1	3.5V Tch start-85 degree	eC
LAIN	040	1110			5 0,
	V _{CC} -V _{CC} V _{load dump} I _L	VCC 28 -VCC -16 V _{load dump} 42 IL Self limited PD 3.10 VIN Vcc-28 Vcc+16 Vsc+16 VIS -2 to VCC -16 -16 IIS(Rev) -30 Tch -40 to +150 Tstg -55 to +150 VESD 2000 4000 200 EAS 1700	VCC 28 V -VCC -16 V V _{load dump} 42 V IL Self limited A PD 3.10 W VIN Vcc-28 V Vcc+16 V VIS -2 to VCC V -16 V IIS(Rev) -30 mA Tch -40 to +150 degreeC Tstg -55 to +150 degreeC VESD 2000 V EAS 1700 mJ	VCC 28 V -VCC -16 V At nom RIN=10 V _{load dump} 42 V RI=10h RIN=10 IL Self limited A PD 3.10 W Ta=85c Device with 6 or Device Wi	VCC 28 V -VCC -16 V At nominal load current, t<2min, RIN=100ohm, RIS=1kohm

3.4 Thermal Characteristics

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Thermal characteristics	Rth(ch-a)		21		degree C/W	According to JEDEC JESD51-2, -5, -7 on FR4 2s2p board
	Rth(ch-c)		0.21		degree C/W	

3.5 Electrical Characteristics

Operation function

Tch=-40 to 150degreeC, Vcc=7 to 18V, unless otherwise specified

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition	
Operating Voltage	V _{CC}	4.5		28	V	V _{IN} =0V, RL=Nomina	I load, Refer to 3.6.6
							1
Output Leakage current	I _{L(off)}			0.5	μA	Tch=25 degreeC	VCC=13.5V,
				4.0			IIN=0A,
				13		Tch=-40 to 125	VIS=0V,
						degreeC	VOUT=0V
Standby current	I _{CC(off)}			0.5	μΑ	Tch=25 degreeC	VCC=13.5V,
							IIN=0A,
							VIS=0V,
				1.5		Tch=-40 to 85	VOUT=0V
						degreeC	
On-state resistance	Ron		1.6	2.0	mohm	Tch=25 degreeC	IL= Nominal current,
				3.7		Tch=150 degreeC	Refer to 3.6.6
Input current in on state	IIH		2.5	5	mA	-	
Input current for turn-off	IIL			30	μA		
Cranking mode voltage	V _{CC(cr)}			4.5	V		
On-state resistance at	Ron(cr)			8	mohm	VCC=3.2V, RIN=100	ohm,
cranking						Tch=25 degreeC,	
						Pulse duration=24ms	s, IL=Nominal current
						Refer to 3.6.6	
Operating Voltage range	V _{CC(Uv,}	3.2				RIN=100ohm, Tch=2	
for cranking	cr)						s, IL=Nominal current
						Refer to 3.6.6	
Under voltage shutdown	V _{CC(Uv)}			4.5	V		
Under voltage restart	V _{CC(Cpr)}			4.5	V		
Turn on time	ton		500	1000	μs	VCC=13.5V, RL=Nor	ninal load,
Turn on delay time	td(on)		100	200	μs	Refer to 3.6.6	
Turn off time	toff		310	800	μs	-	
Turn off delay time	td(off)		200	500	μs	-	
Slew rate on	dV/dton		0.05	0.1	V/µs		
Slew rate off	-dV/dtoff		0.14	0.3	V/µs		
Turn on energy loss 1)	Eon		30		mJ	VCC=13.5V, Tch=25	degreeC,
Turn off energy loss 1)	Eoff		11		mJ	RL=Nominal load,	
						Refer to 3.6.6	
Driving capability 1)	Dr(capa)	75			mohm	Tch=25 degreeC, VC	
		100				Tch=105 degreeC, V	CC=8 to16V

¹⁾ not subjected production test, guaranteed by design

Protection function

Tch=-40 to 150degreeC, Vcc=7 to 18V, unless other wise specified

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditi	on
Over current detection current	IL(SC)	150	260		Α	VCC=13.5V	, Von=5V, Tch=25 degreeC
Current limitation under power limitation toggling	IL(CL)		90		А	VCC=13.5V	
Sense current output trigger threshold	Von(CL1)		1.0		V	VCC=13.5V	
Current limitation trigger threshold during on-state	Von(CL2)		0.3		V	VCC=13.5V	
Turn-on check delay after input signal positive slope	td(CL)		1.6		ms	VCC=13.5V	
Absolute thermal shutdown temperature	aTth	150			degreeC		
Power limitation thermal shutdown temperature	dTth		40		degreeC		
Power limitation restart temperature	dTth,rest art		19		degreeC		
Output clamp at inductive load switch off	Von,clam p	30		40	V	VCC=13.5V degreeC	, IL=40mA, Tch=25
On-state resistance at reverse battery condition	Ron(rev)			2.5	mohm	Tch=25 degreeC	VCC=-13.5V, IL=Nominal current,
				4.6		Tch=150 degreeC	Refer to 3.6.6
IN current at reverse battery condition	IIN(rev)		-2		mA	VCC=-16V,	Tch=25 degreeC

Diagnosis function

Tch=-40 to 150degreeC, Vcc=7 to 18V, unless other wise specified

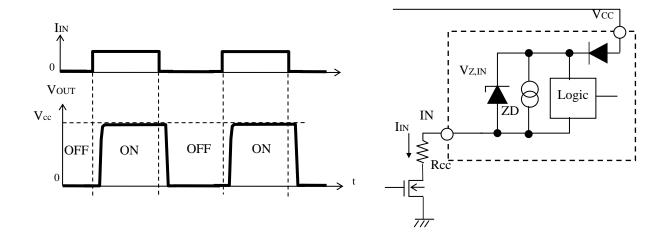
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Current sense ratio	KILIS	35000	70000	110000		IL= 16.5 A
		40000	70000	105000		IL= 33 A
Current sense drift	dKILIS	-20		20	%	VCC=13.5V, Tch,start=25 degreeC,
depends on temperature						IL =33A, Refer to 3.6.6
Sense current offset	lis,offset			50	μΑ	IL=0A, Tch =25 degreeC
current						
Sense current under fault	lis,fault	5.0			mΑ	VCC=13.5V, RIS=1kohm
condition		4.3				VCC=13.5V, RIS=2kohm
Load current to output	IL,min	3.5			Α	VCC=13.5V, Tch=25degreeC,
sense current						IIS>1uA
Sense current settling time	tsis(on)		500	1100	μs	VCC=13.5V, IIN=IIL to IIH,
after input signal positive						IL/IIS=KILIS, RL=Nominal load,
slope						Refer to 3.6.6
Sense current settling time	tsis(off)			10	μs	IIN=IIH to IIL
after input signal negative						
slope 1)						
Sense current settling time	tsis(LC)			50	μs	RL= 2 * Nominal load to Nominal
during on-state 1)						load,Refer to 3.6.6
Fault signal delay after	tdsc(fault)			10	μs	IIN=IIL to IIH, IL=IL(SC)
over current detection 1)						
Fault signal delay after	tdpl(fault)			10	μs	Von>Von(CL1)
power limitation valid 1)						
Fault signal delay after	tdpl(off)			30	μs	Von <von(cl1)< td=""></von(cl1)<>
power limitation invalid 1)						
Fault signal delay after	tdot(fault)			10	μs	IIS→IIS,fault
absolute thermal shutdown						
1)						
Fault signal delay after	tdoff(fault)			10	μs	IIN=IIH to IIL
input negative slope 1)						

¹⁾ not subjected production test, guaranteed by design

3.6 Feature Description

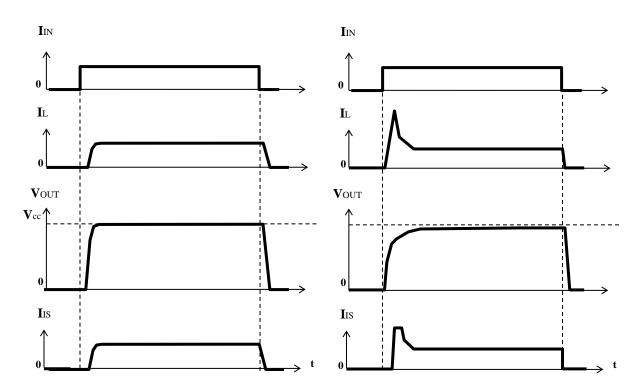
3.6.1 Driving Circuit

The high-side output is turned on, if the input pin is connected to ground through a low impedance path allowing a current of IIH. The high-side output is turned off, if the input current gets below IIL

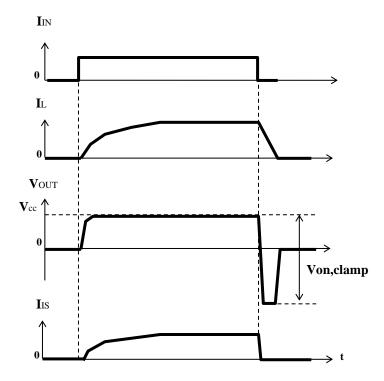


Switching a resistive load

Switching lamps



Switching an inductive load

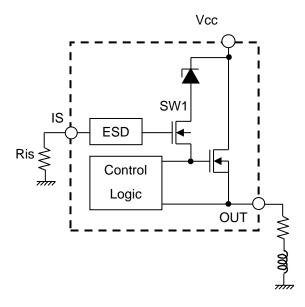


The dynamic clamp circuit works only when the inductive load is switched off. When the inductive load is switched off, the voltage of OUT falls below 0V. The gate voltage of SW1 is then nearly equal to GND. Next, the voltage at the source of SW1 (= gate of output MOS) falls below the GND voltage.

SW1 is turned on, and the clamp diode is connected to the gate of the output MOS, activating the dynamic clamp circuit.

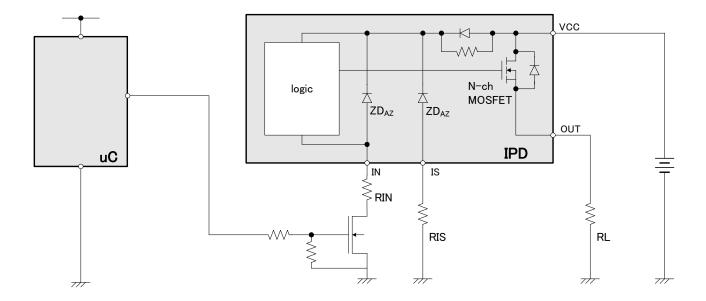
When the over-voltage is applied to VCC, the gate voltage and source voltage of SW1 are both nearly equal to GND. SW1 is not turned on, the clamp diode is not connected to the gate of the output MOS, and the dynamic clamp circuit is not activated.

The dynamic clamp works only if IS pin is connected to GND through a resistor.



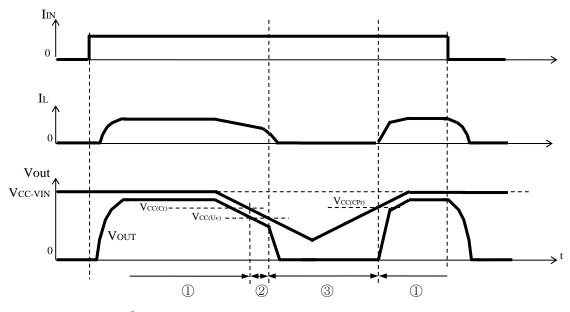
3.6.2 Device behavior at over voltage condition

In case of supply voltage greater than Vload dump, logic part is clamped by ZD_{AZ} (35V min). And current through of logic part is limited by external ground resistor. In addition, the power transistor switches off in order to protect the load from over voltage. Permanent supply voltage than V_{load} dump must not be applied to VCC.



3.6.3 Device behavior at low voltage condition

If the voltage supply $(V_{CC}-V_{IN})$ goes down under $V_{CC}(Uv)$, the device outputs shuts down. If voltage supply $(V_{CC}-V_{IN})$ increase over $V_{CC}(Cpr)$, the device outputs turns back on automatically. The device keeps off state after under voltage shutdown. The IS output is cleared during off-state.



① : Normal operating mode

② : Cranking mode

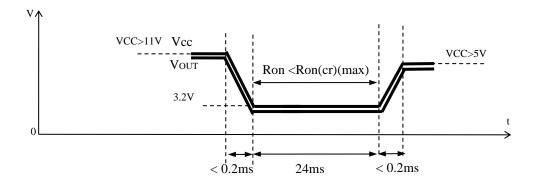
③ : Under voltage mode

Availability of each function in each mode

○: Enable, ×: Disable

	Function	1)	2	3	Note
Normal operation	Turn on	0	×	×	
Normal operation	Turn off	0	0		
Normal operation	Keep on-state	0	O ^(*1)	×	(*1)Ron is defined as Ron(Cr).
Normal operation	KILIS function	0	×	×	In case of Von < Von(CL1)
Diagnosis	Von(CL1), td(CL)	0	×	×	Refer to 3.6.4
Protection	IL(SC)	0	×	×	Refer to 3.6.4
Protection	Von(CL2)	0	×	×	Refer to 3.6.4
Protection	aTch	0	0		Refer to 3.6.4
Protection	dTch	0	×	×	Refer to 3.6.4
Protection	Von(CL1)	×	0	0	Refer to 3.6.4

Definition of on-state resistance at cranking



3.6.4 Short circuit protection

Turn-on in an over load condition including short circuit condition

The device shuts down automatically when condition (a) or (c) is detected. The sense pin output Iis,fault. Shutdown is latched until the next reset via input pin. The device shuts down automatically when condition (b) is detected. The device restarts automatically in power limitation mode. The sense pin output Iis,fault when (d) is detected.

- (a) IL > IL(SC)
- (b) deltaTch > dTth
- (c) Tch > aTth
- (d) Von > Von(CL1) after td(CL)

Over load condition including short circuit condition during on-state

The device runs automatically into power limitation mode when condition (e) is detected once after Von < Von(CL2). The device shuts down automatically when condition (f) is detected. The device restarts automatically in power limitation mode. The sense pin output Iis,fault during power limitation mode. The device shuts down automatically when condition (g) or (h) is detected. The sense pin output Iis,fault Shutdown is latched until the next reset via input pin.

- (e) Von > Von(CL2)
- (f) deltaTch > dTth
- (g) Tch > aTth
- (h) IL > IL(SC)

Power limitation control

Current limitation control with IL(CL) when auto restart from deltaTch protection.

During toggling mode due to Delta Tch protection, if Von>Von(CL1) or if the current is limited to IL(CL), the sense pin output Iis, fault. If Von<Von(CL2) and if the short current is not high enough to reach IL(CL) during toggling mode with delta Tch protection, then the sense pin outputs sense current at on-state and Iis,fault at off state.

delta Tch

Junction temperature differences between thermal sensors of power area.

3.6.5 Diagnostic signal

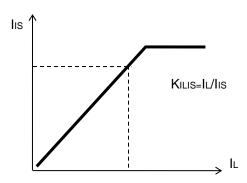
Truth table

	Input current	Output	Diagnostic output
Normal Operation	Н	VCC	IIS = IL/KILIS
Tromai operation	L	L 1)	$L^{2)}$
Shutdown by over	Н	L 1)	lis,fault ³⁾
current detection	L	L 1)	L ²⁾
Power limitation	Н	VOUT 6)	IIS = IL/KILIS in case of Von <von(cl1)< td=""></von(cl1)<>
		7001	Iis,fault 4) in case of Von>Von(CL1)
1 ower mintation		L 1)	Iis,fault ⁴⁾
	L	L 1)	L 2)
Shutdown by over absolute channel	Н	L 1)	Iis,fault ⁵⁾
temperature detection	L	L 1)	$L^{2)}$
Short circuit to	Н	VCC	<iis< td=""></iis<>
VCC	L	VOUT 7)	L ²⁾

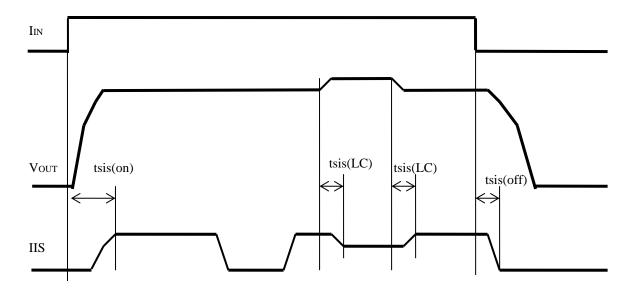
- 1) In case of OUT terminal is connected to GND via load.
- 2) In case of IS terminal is connected to GND via resister.
- 3) IS terminal keeps Iis, fault as long as input signal activate after the over current detection.
- 4) IS terminal keeps Iis,fault during power limitation if Von>Von(CL1).
- 5) IS terminal keeps Iis, fault as long as input signal activate after over absolute channel temperature detection.
- 6) VOUT depends on the short circuit condition.
- 7) VOUT depends on the ratio of VCC-OUT-GND resistive component.

Current sense output

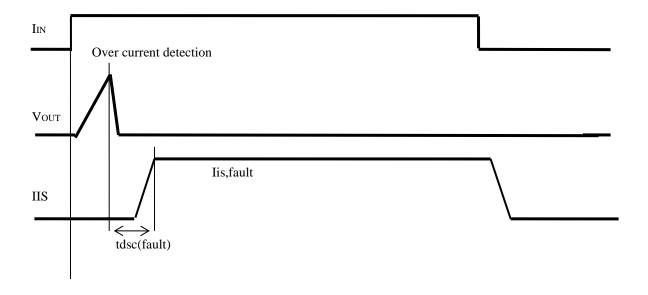
The device output analog feedback current proportional to output current from IS pin. In the case of much higher current than nominal load current, current sense output is saturated.



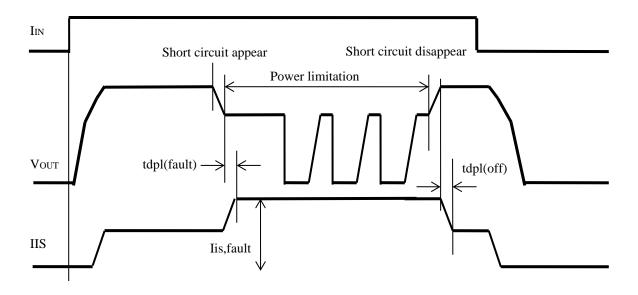
Sense voltage setting time



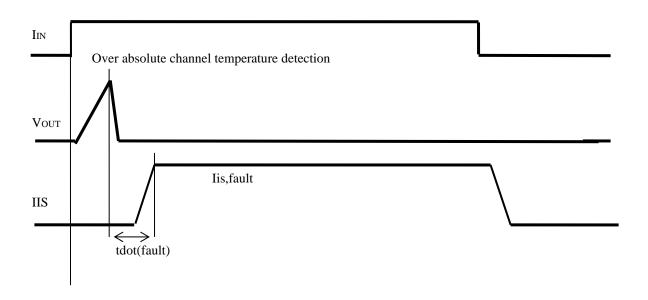
Fault signal delay time at over current detection



Fault signal delay time at power limitation



Fault signal delay time at over absolute channel temperature detection

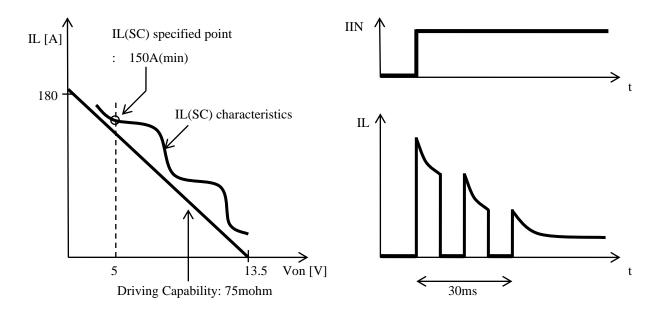


3.6.6 Nominal load and nominal current

Parameter	Values	Condition
Nominal load	0.5ohm	$Tj \leq 150 \text{ degreeC}$
Nominal current	33A	$Tj \leq 150 \text{ degreeC}$

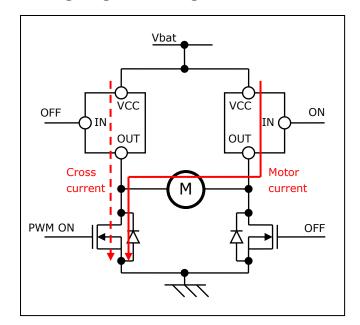
3.6.7 Driving Capability

Driving Capability is specified as load impedance. Over current detection characteristics is designed above Driving Capability characteristics. If estimated load impedance which comes from peak inrush current is lower than Driving Capability characteristics, this means, the device does not detect inrush current as over current and does not shutdown the output. Depend on the conditions, Power Limitation function may work during inrush current. If estimated load impedance which comes from peak inrush current is lower than Driving Capability characteristics, Power limitation disappear within 30ms. This parameter does not mean that the device can drive the resistive load up to Driving Capability characteristics.



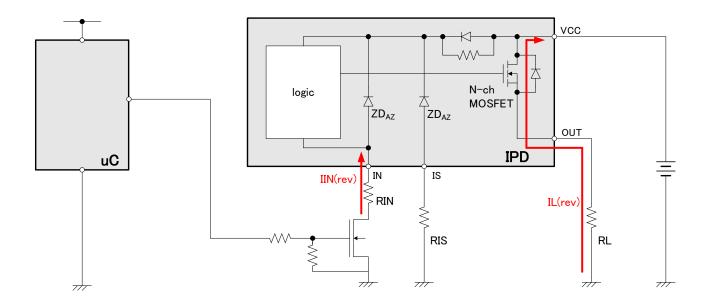
3.6.8 Cross current protection in case of H-bridge high side usage

In case of using High side driver in H-bridge circuit, High side driver protects High side driver itself and also low side driver from high power dissipation by cross current when low side driver switching on.



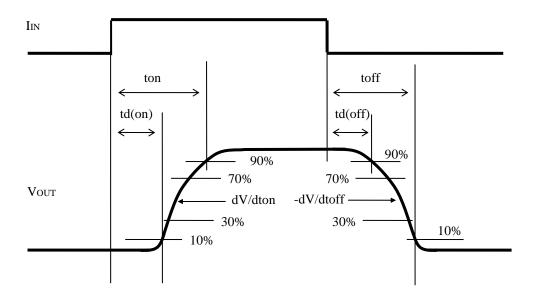
3.6.9 Reverse Battery Protection by turn on the output

In case of a reverse battery is applied to the device, the N-ch MOSFET will turn on only if reverse current flow from IN pin. The reverse current through the N-ch MOSFET has to be limited by the connected load. IIN(rev) is limited internally approx. 2mA even without external RIN. Reverse current flow from IS should be limited by external component such as recommendation value in Pin function, refer 3.2 Pin configuration.



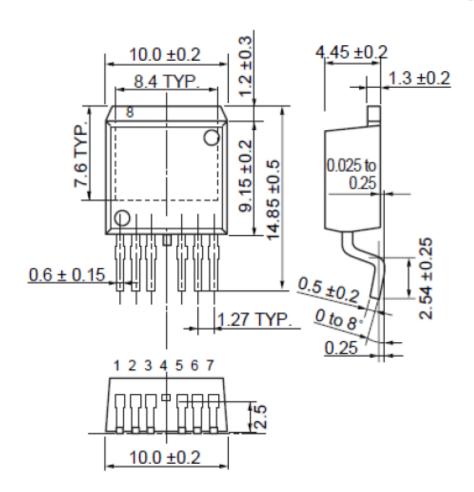
3.6.10 Measurement condition

Switching waveform of OUT terminal

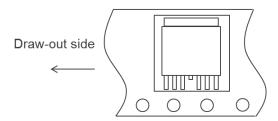


3.7 Package drawing

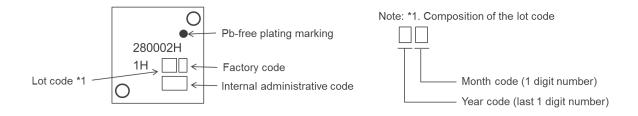
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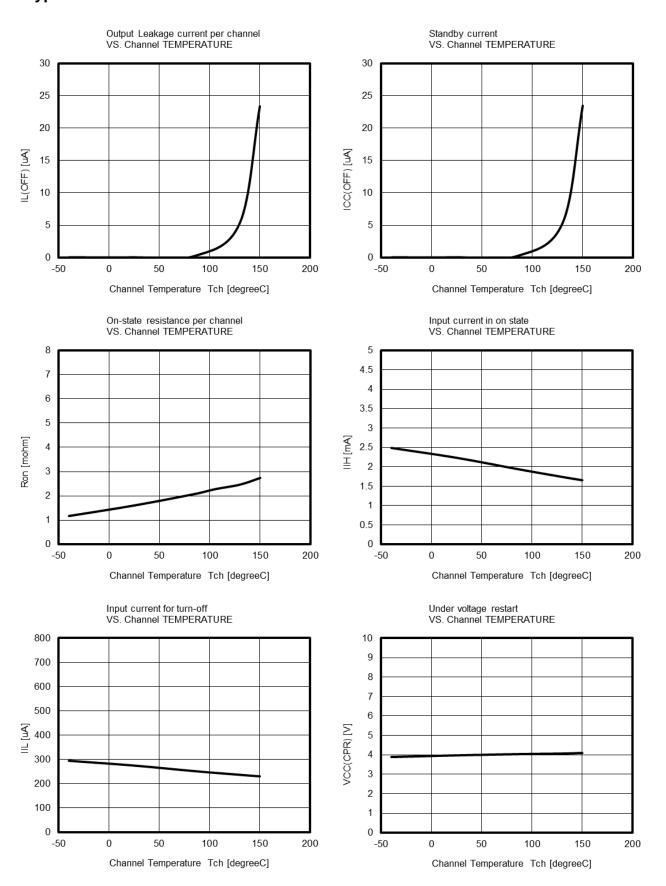
3.8 Taping information

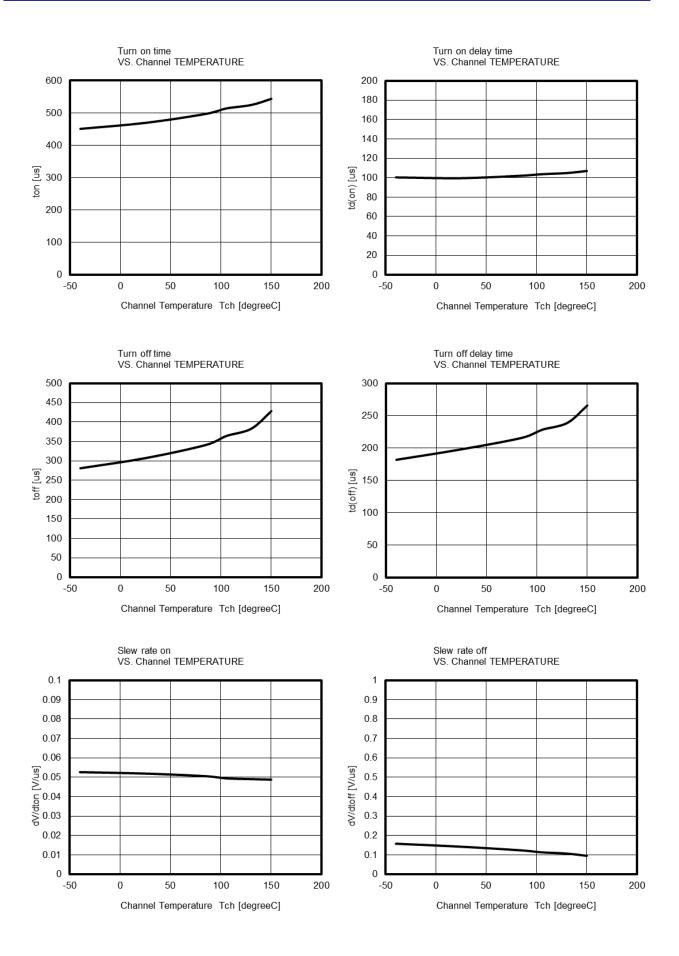


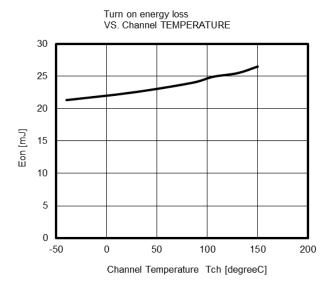
3.9 Marking information

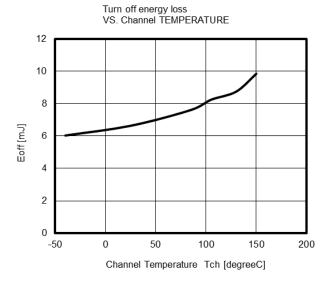


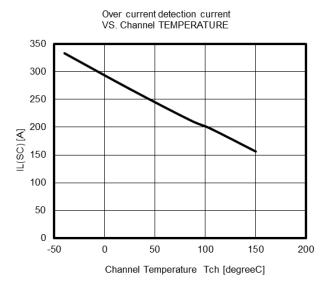
4 Typical characteristics

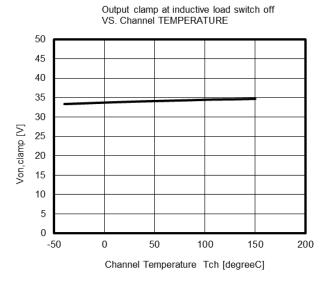


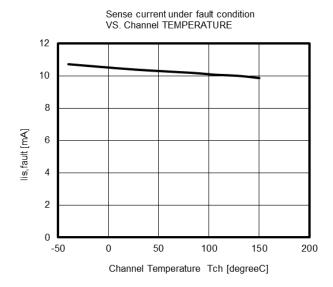






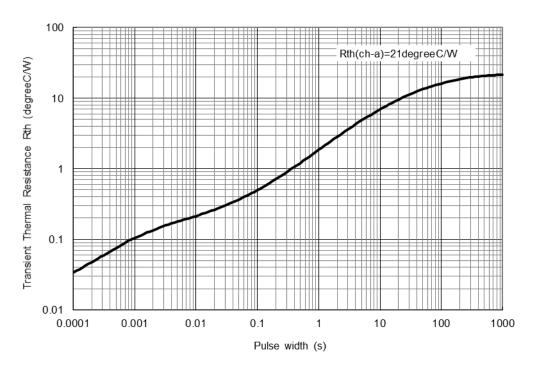




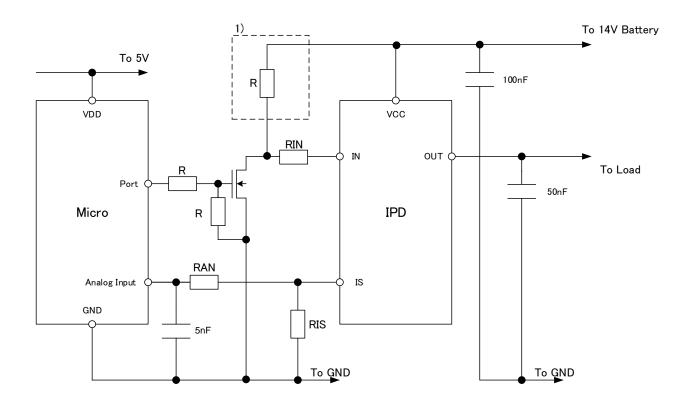


5 Thermal characteristics

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



6 Application example in principle



RAN value is in range of 2k to 50kohm depending microcontroller. 100ohm is recommended as RIN. If necessary to raise HBM tolerated dose, adding resister between OUT terminal and Ground is effective. Resister's value is typically 100kohm

1) In order to prevent leakage current through at IN terminal via PCB, it is recommended to pull up the IN terminal to VCC using around 1 to 10 kohm (approx.) resistor.

Revision History

RAJ2800024H11HPF Datasheet

		Description		
Rev.	Date	Page	Summary	
1.00	Aug. 1, 2017	1-26	1st issue	
1.01	Feb. 14, 2022	all	Typo corrected.	

All documents should contain the following section break and paragraph as the last item. The footers of this document refer to the paragraph in order to reference the last page of the document.

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